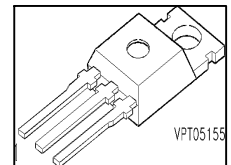


Cool MOS™ Power Transistor
Feature

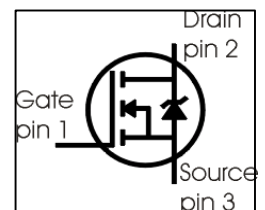
- New revolutionary high voltage technology
- Worldwide best $R_{DS(on)}$ in TO 220
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- High peak current capability
- Intrinsic fast-recovery body diode
- Extreme low reverse recovery charge
- **Pb-free lead plating; RoHS compliant; Halogen free mold compound**
- **Qualified for industrial grade applications according to JEDEC⁰⁾**

$V_{DS} @ T_{jmax}$	650	V
$R_{DS(on)}$	0.22	Ω
I_D	20.7	A

PG-TO220



Type	Package	Ordering Code	Marking
SPP20N60CFD	PG-TO220	Q67040-S4616	20N60CFD


Maximum Ratings

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$	I_D	20.7 13.1	A
Pulsed drain current, t_D limited by T_{jmax}	$I_{D\text{ puls}}$	52	
Avalanche energy, single pulse $I_D = 10\text{ A}, V_{DD} = 50\text{ V}$	E_{AS}	690	mJ
Avalanche energy, repetitive t_{AR} limited by T_{jmax} ¹⁾ $I_D = 20\text{ A}, V_{DD} = 50\text{ V}$	E_{AR}	1	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	20	A
Reverse diode dv/dt $I_S = 20.7\text{ A}, V_{DS} = 480\text{ V}, T_j = 125\text{ °C}$	dv/dt	40	V/ns
Gate source voltage	V_{GS}	± 20	V
Gate source voltage AC ($f > 1\text{ Hz}$)	V_{GS}	± 30	
Power dissipation, $T_C = 25\text{ °C}$	P_{tot}	208	W
Operating and storage temperature	T_j, T_{sta}	-55... +150	°C

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 480 \text{ V}$, $I_D = 20.7 \text{ A}$, $T_j = 125 \text{ }^\circ\text{C}$	dv/dt	80	V/ns
Maximum diode commutation speed $V_{DS} = 480 \text{ V}$, $I_D = 20.7 \text{ A}$, $T_j = 125 \text{ }^\circ\text{C}$	di_F/dt	900	A/ μs

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	0.6	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	$^\circ\text{C}$

Electrical Characteristics, at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}$, $I_D=0.25\text{mA}$	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{V}$, $I_D=20\text{A}$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=1000\mu\text{A}$, $V_{GS}=V_{DS}$	3	4	5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600\text{V}$, $V_{GS}=0\text{V}$, $T_j=25^\circ\text{C}$, $T_j=150^\circ\text{C}$	-	2.1 1700	-	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$, $I_D=13.1\text{A}$, $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	0.19 0.51	0.22 -	Ω
Gate input resistance	R_G	$f=1\text{MHz}$, open Drain	-	0.54	-	

Electrical Characteristics , at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	g_{fs}	$V_{DS} \geq 2 * I_D * R_{DS(on)max}$ $I_D = 13.1\text{A}$	-	17.5	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	2400	-	pF
Output capacitance	C_{oss}		-	780	-	
Reverse transfer capacitance	C_{rss}		-	50	-	
Effective output capacitance, ²⁾ energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V to } 480\text{V}$	-	83	-	pF
Effective output capacitance, ³⁾ time related	$C_{o(tr)}$		-	160	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 380\text{V}$, $V_{GS} = 0/10\text{V}$, $I_D = 20.7\text{A}$, $R_G = 3.6\Omega$	-	12	-	ns
Rise time	t_r		-	15	-	
Turn-off delay time	$t_{d(off)}$		-	59	-	
Fall time	t_f		-	6.4	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 480\text{V}$, $I_D = 20.7\text{A}$	-	15	-	nC
Gate to drain charge	Q_{gd}		-	54	-	
Gate charge total	Q_g	$V_{DD} = 480\text{V}$, $I_D = 20.7\text{A}$, $V_{GS} = 0\text{ to } 10\text{V}$	-	95	124	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 480\text{V}$, $I_D = 20.7\text{A}$	-	7	-	V

⁰J-STD20 and JESD22

¹Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} * f$.

² $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

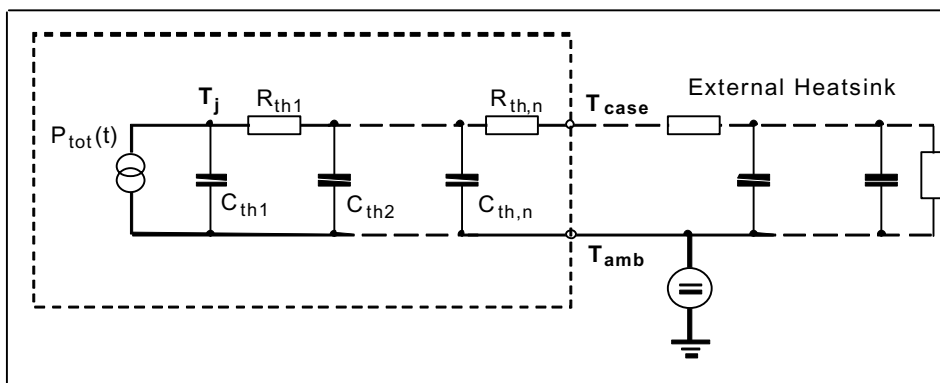
³ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	$T_C=25^\circ\text{C}$	-	-	20.7	A
Inverse diode direct current, pulsed	I_{SM}		-	-	52	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=480\text{V}, I_F=I_S,$	-	150	-	ns
Reverse recovery charge	Q_{rr}	$di_F/dt=100\text{A}/\mu\text{s}$	-	1	-	μC
Peak reverse recovery current	I_{rrm}		-	13	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	1400	-	$\text{A}/\mu\text{s}$

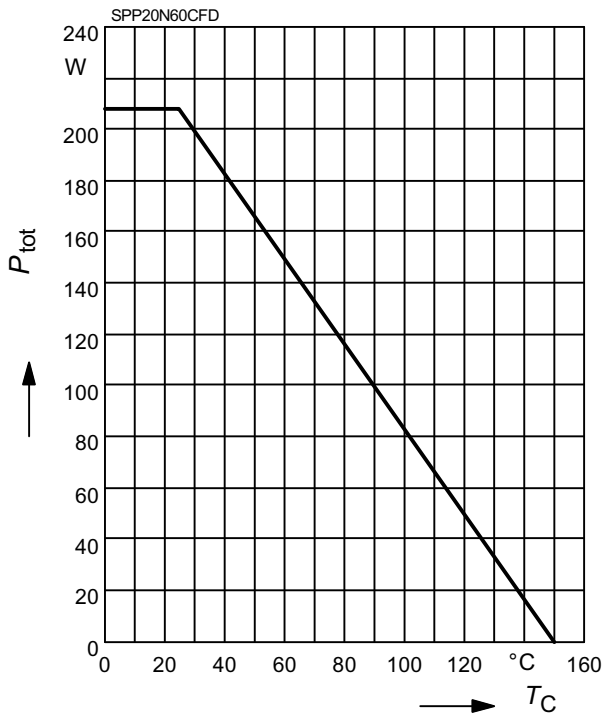
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.007686	K/W	C_{th1}	0.0003764	Ws/K
R_{th2}	0.015		C_{th2}	0.001412	
R_{th3}	0.029		C_{th3}	0.001932	
R_{th4}	0.114		C_{th4}	0.005299	
R_{th5}	0.136		C_{th5}	0.012	
R_{th6}	0.059		C_{th6}	0.091	



1 Power dissipation

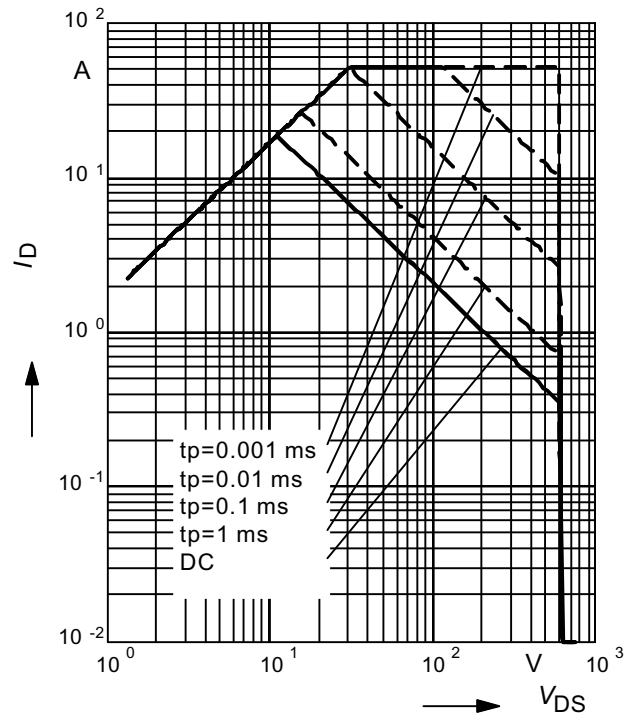
$$P_{tot} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS})$$

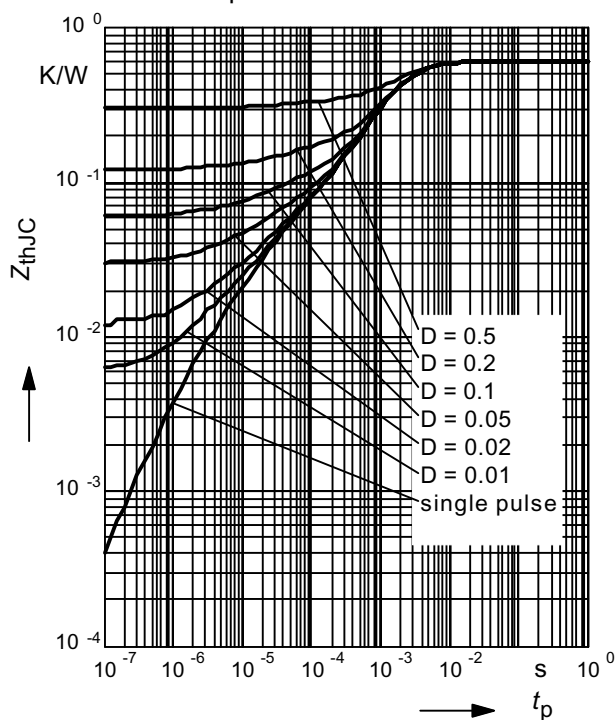
parameter : $D = 0, T_C = 25^\circ\text{C}$



3 Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

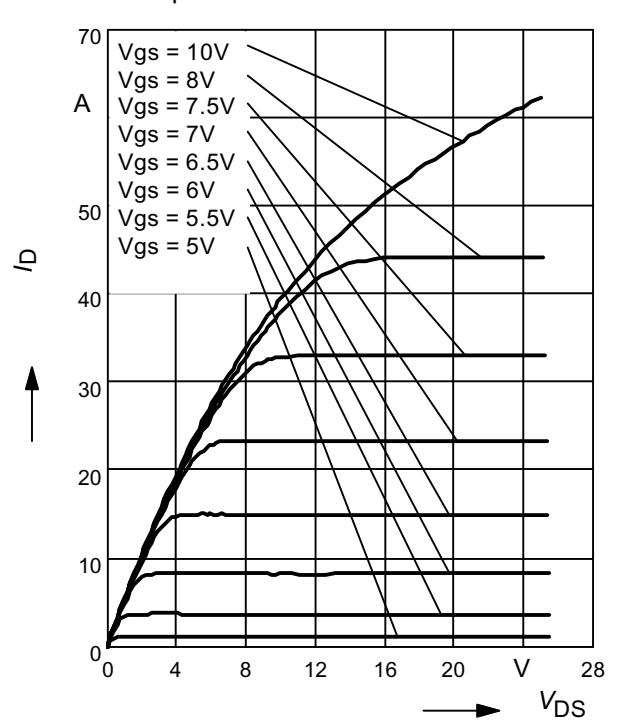
parameter: $D = t_p/T$



4 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

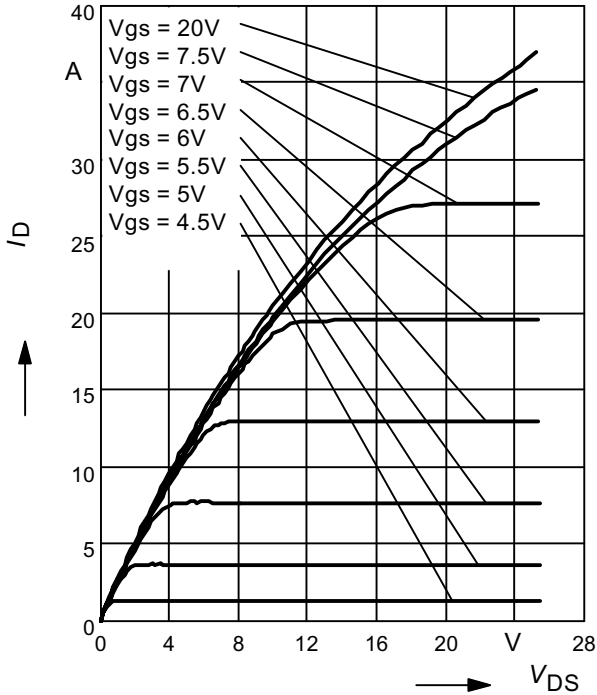
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



5 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$

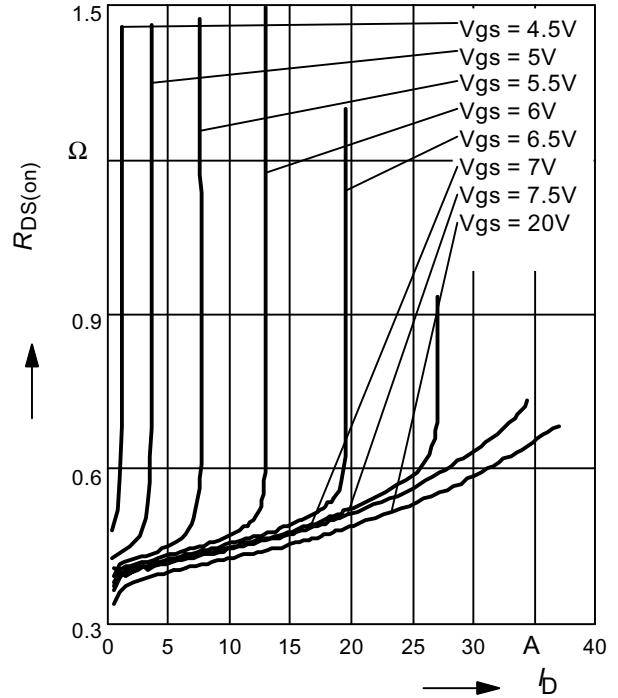
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

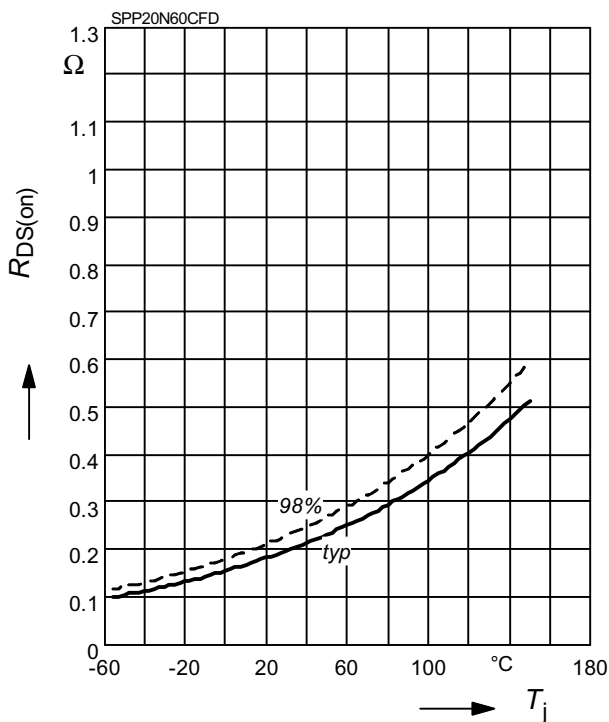
parameter: $T_j = 150^\circ\text{C}, V_{GS}$



7 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

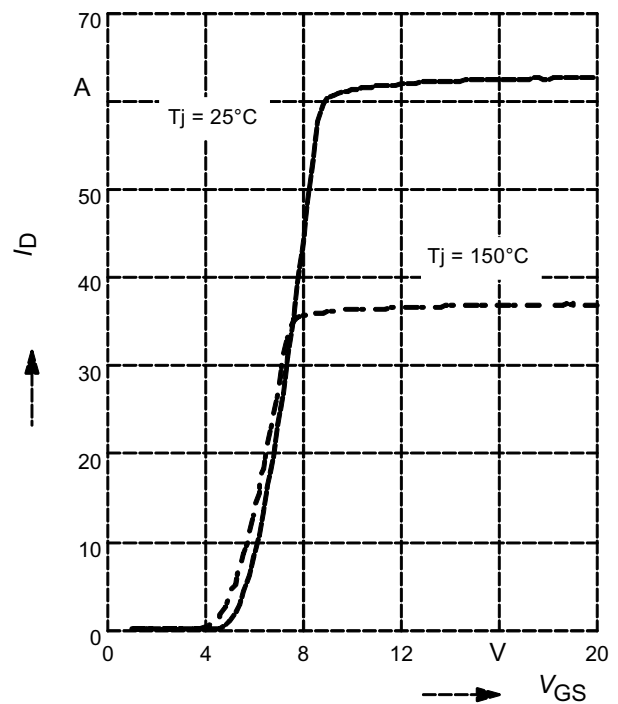
parameter: $I_D = 13.1 \text{ A}, V_{GS} = 10 \text{ V}$



8 Typ. transfer characteristics

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

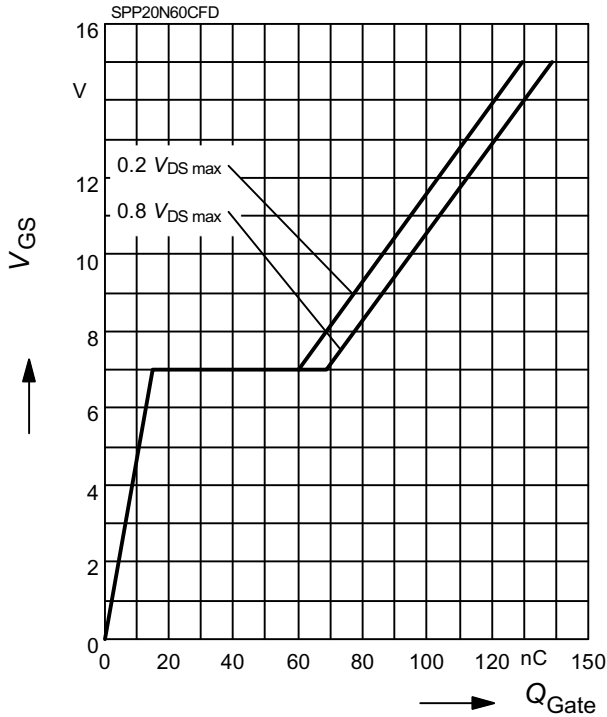
parameter: $t_p = 10 \mu\text{s}$



9 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

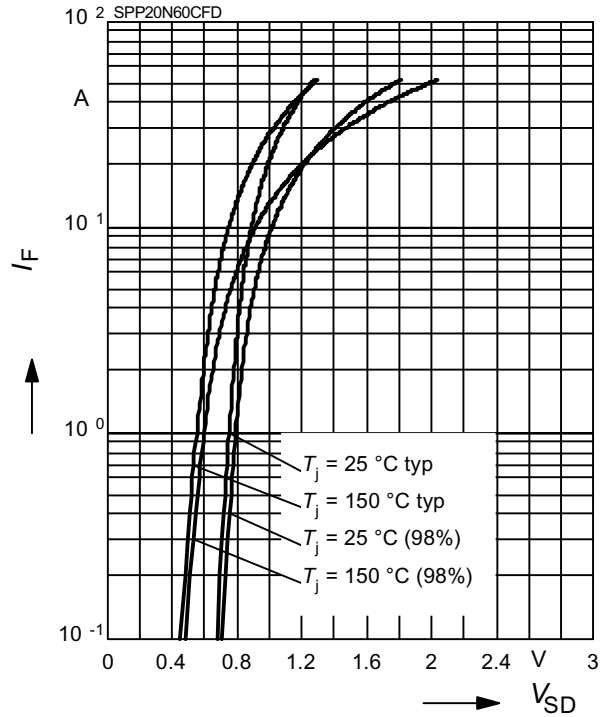
parameter: $I_D = 20.7 \text{ A}$ pulsed



10 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

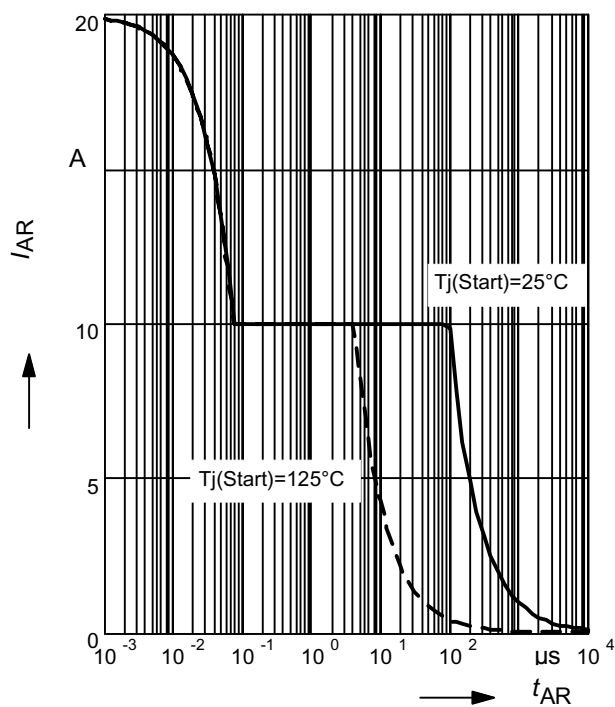
parameter: $T_j, t_p = 10 \mu\text{s}$



11 Avalanche SOA

$$I_{AR} = f(t_{AR})$$

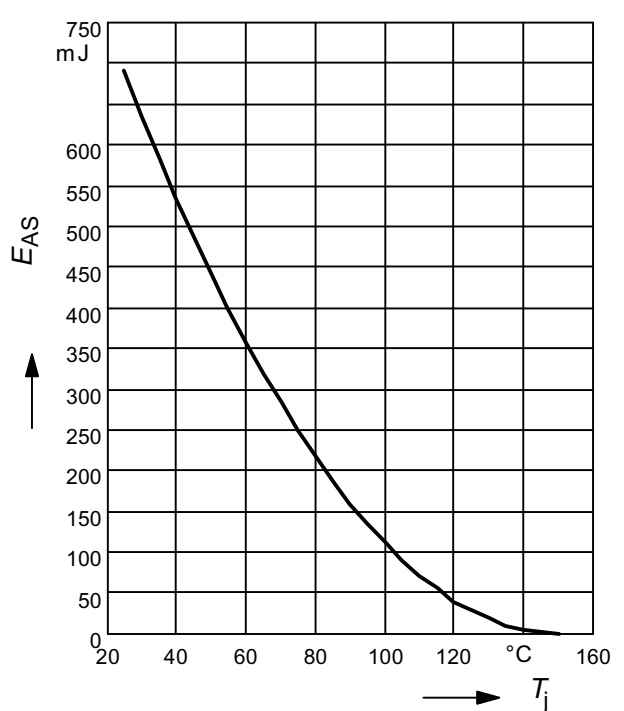
par.: $T_j \leq 150 \text{ °C}$



12 Avalanche energy

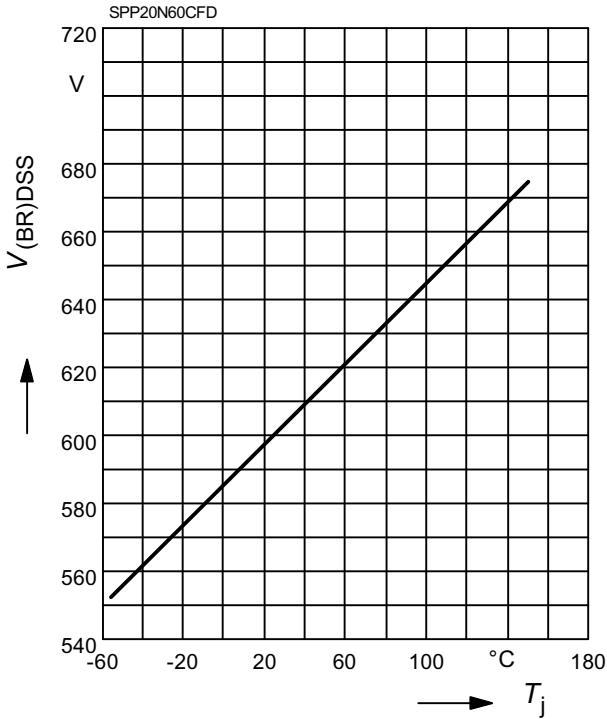
$$E_{AS} = f(T_j)$$

par.: $I_D = 10 \text{ A}, V_{DD} = 50 \text{ V}$



13 Drain-source breakdown voltage

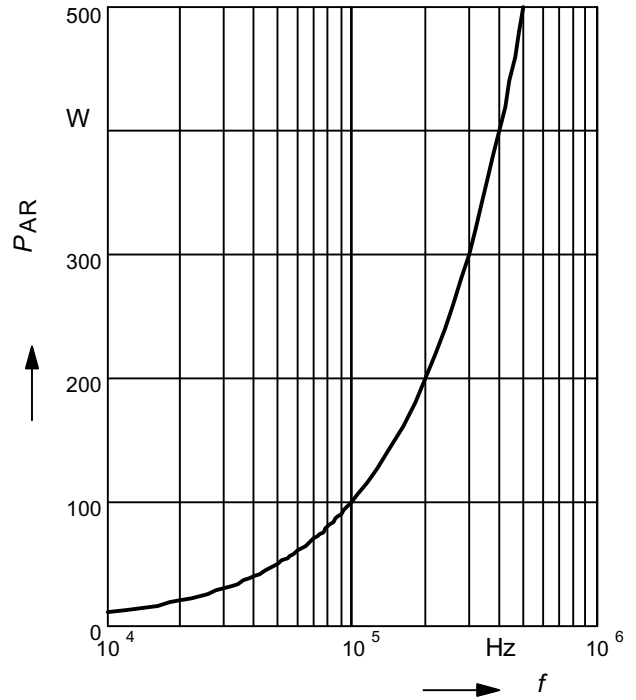
$$V_{(BR)DSS} = f(T_j)$$



14 Avalanche power losses

$$P_{AR} = f(f)$$

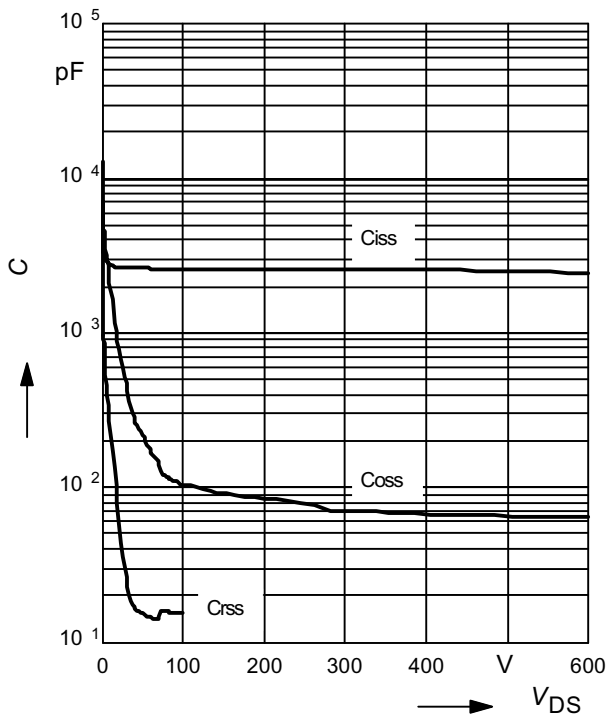
parameter: $E_{AR}=1mJ$



15 Typ. capacitances

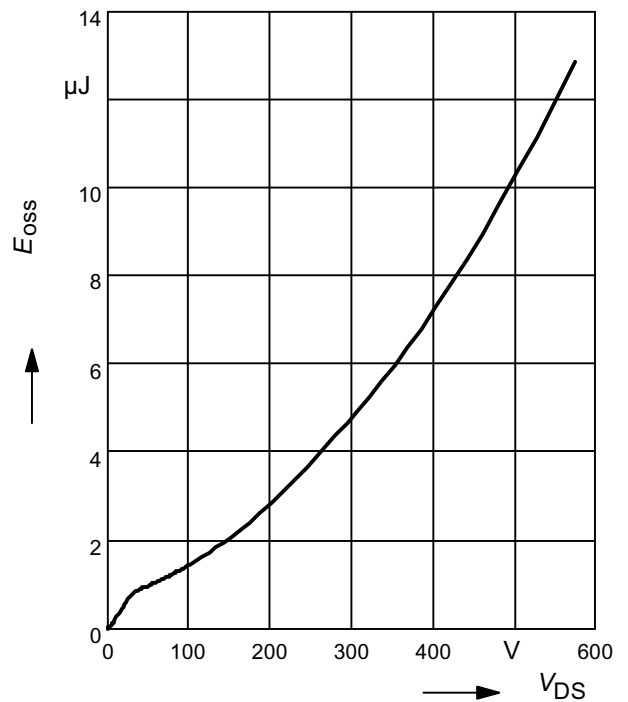
$$C = f(V_{DS})$$

parameter: $V_{GS}=0V, f=1 MHz$



16 Typ. C_{oss} stored energy

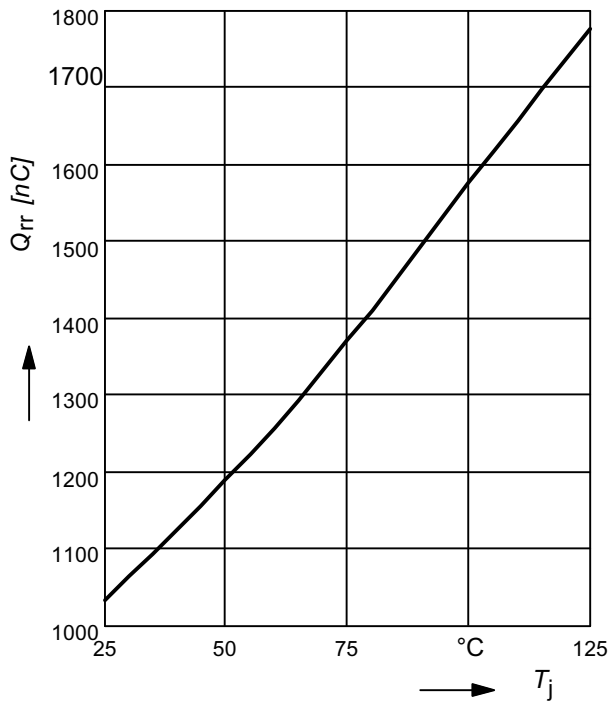
$$E_{oss} = f(V_{DS})$$



17 Typ. reverse recovery charge

$$Q_{rr} = f(T_j)$$

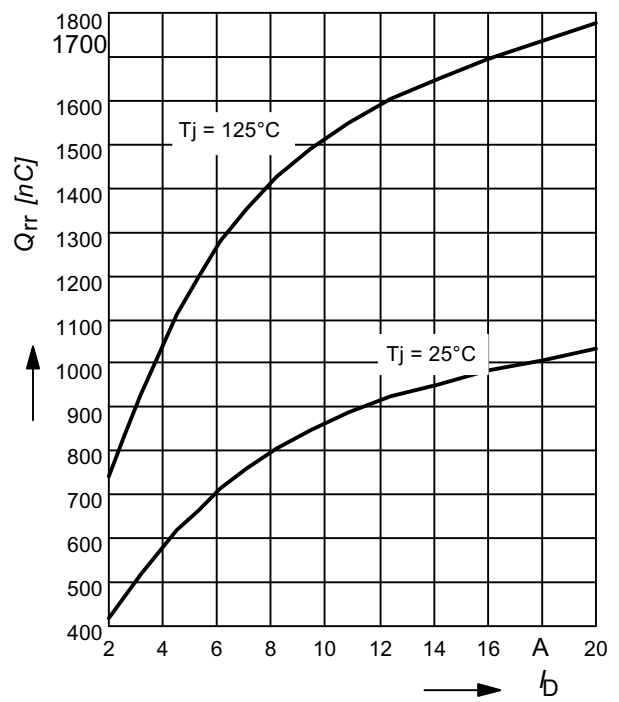
parameter: $I_D = 20.7A$



18 Typ. reverse recovery charge

$$Q_{rr} = f(I_D)$$

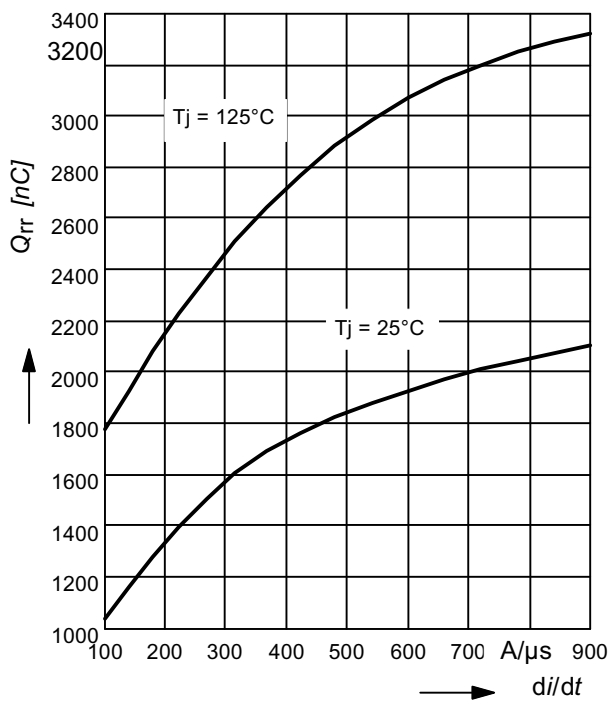
parameter: $di/dt = 100 A/\mu s$



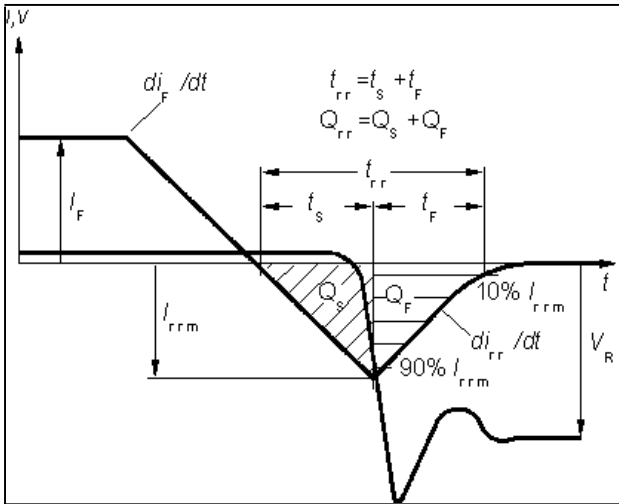
19 Typ. reverse recovery charge

$$Q_{rr} = f(di/dt)$$

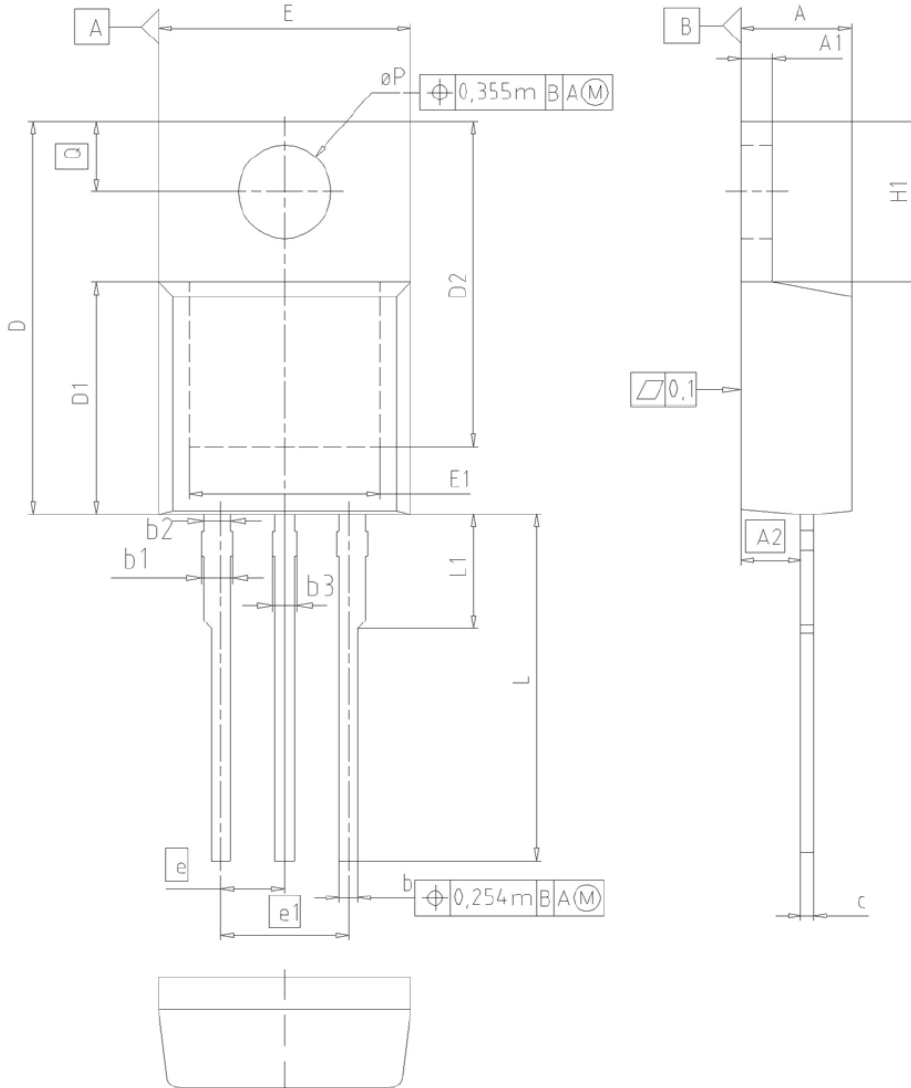
parameter: $I_D = 20.7 A$



Definition of diodes switching characteristics



PG-TO-220-3-1, PG-TO220-3-21



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
ϕP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

DOCUMENT NO.
Z8B00003318

SCALE

EUROPEAN PROJECTION

ISSUE DATE
23-08-2007

REVISION
05

Published by
Infineon Technologies AG
81726 Munich, Germany
© 2007 Infineon Technologies AG
All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.



Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331